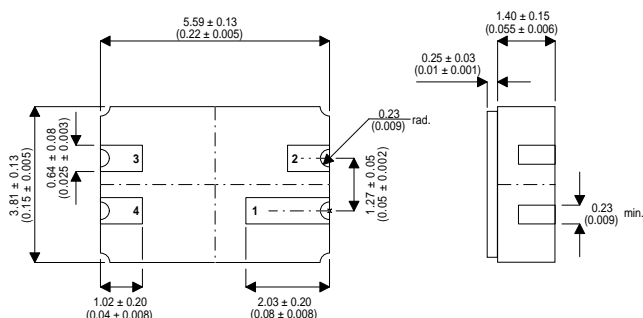


**HIGH SPEED PNP  
MEDIUM VOLTAGE TRANSISTOR IN A  
CERAMIC SURFACE MOUNT PACKAGE**

**MECHANICAL DATA**

Dimensions in mm (inches)



**FEATURES**

- CERAMIC SURFACE MOUNT HERMETIC PACKAGE
- LOW WEIGHT
- SMALL FOOTPRINT
- SCREENING OPTIONS AVAILABLE

**LCC3 PACKAGE  
Underside View**

PAD 1 – Collector      PAD 3 – Emitter  
PAD 2 – N/C          PAD 4 – Base

**ABSOLUTE MAXIMUM RATINGS**  $T_{case} = 25^{\circ}C$  unless otherwise stated

$V_{CEO}$	Collector – Emitter Voltage	-80V
$V_{CBO}$	Collector – Base Voltage	-80V
$V_{EBO}$	Emitter – Base Voltage	-5V
$I_C$	Continuous Collector Current	-1A
$P_D$	Total Device Dissipation at $T_A = 25^{\circ}C$	400mW
	Derate above $25^{\circ}C$	2.28 mW/ $^{\circ}C$
$T_{stg}$	Operating and Storage Temperature Range	-55 to +200 $^{\circ}C$

**ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CBO}$ Collector Cut Off Current	$V_{CB} = -60V$ $T_A = 150^{\circ}C$			-50	nA
				-50	$\mu A$
$I_{EBO}$ Emitter Cut Off Current	$V_{EB} = -5V$			-10	$\mu A$
$V_{CE(sat)}$ Collector Emitter Saturation Voltage <sup>1</sup>	$I_C = -150mA$ $I_B = -15mA$			-0.15	V
	$I_C = -500mA$ $I_B = -50mA$			0.50	
$V_{BE(sat)}$ Base Emitter Saturation Voltage <sup>1</sup>	$I_C = -150mA$ $I_B = -15mA$			-0.9	V
$V_{BE(on)}$ Base Emitter on Voltage	$I_C = -500mA$ $V_{CE} = -0.5V^1$			-1.1	V
$V_{(BR)CEO}$ Collector Emitter Breakdown Voltage	$I_C = -10mA$	-80			V
$V_{(BR)CBO}$ Collector Base Breakdown Voltage	$I_C = -10\mu A$	-80			V
$V_{(BR)EBO}$ Emitter Base Breakdown Voltage	$I_E = -10\mu A$	-5.0			V
$h_{FE}$ DC Current Gain	$I_C = -100mA$ $V_{CE} = -5.0V$ @-55°C <sup>1</sup>	40			—
	$I_C = -100\mu A$ $V_{CE} = -5.0V$	75			
	$I_C = -100mA$ $V_{CE} = -5.0V^1$	100		300	
	$I_C = -500mA$ $V_{CE} = -5.0V^1$	70			
	$I_C = -1.0A$ $V_{CE} = -5.0V^1$	25			
<b>SMALL SIGNAL CHARACTERISTICS</b>					
$C_{obo}$ Output Capacitance	$V_{CE} = -10V$ $f = 1MHz$			20	pF
$C_{ibo}$ Input Capacitance	$V_{EB} = -0.5V$ $f = 1MHz$			110	
$h_{fe}$ Small Signal Gain	$I_C = -50mA$ $V_{CE} = -10V$ $f = 100MHz$	1.5		5.0	—
<b>SWITCHING CHARACTERISTICS</b>					
$t_{on}$ Turn On Time	$I_C = -500mA$ $I_{B1} = -I_{B2} = -50mA$			100	ns
$t_f$ Fall Time				50	
$t_s$ Storage Time				350	

<sup>1</sup>Pulse test  $t_p = 300\mu s$ ,  $\delta = 1\%$